**Preferred Device** 

## **Silicon Controlled Rectifiers**

## **Reverse Blocking Thyristors**

Designed primarily for half-wave ac control applications, such as motor controls, heating controls and power supply crowbar circuits.

- Glass Passivated Junctions with Center Gate Fire for Greater Parameter Uniformity and Stability
- Small, Rugged, Thermowatt Constructed for Low Thermal Resistance, High Heat Dissipation and Durability
- Blocking Voltage to 800 Volts
- 300 A Surge Current Capability
- Insulated Package Simplifies Mounting
- N Indicates UL Registered File #E69369
- Device Marking: Logo, Device Type, e.g., MCR225-8FP, Date Code

## **MAXIMUM RATINGS** ( $T_J = 25^{\circ}C$ unless otherwise noted)

Rating	Symbol	Value	Unit
Peak Repetitive Off–State Voltage <sup>(1)</sup> (T <sub>J</sub> = -40 to +125°C, Sine Wave, 50 to 60 Hz, Gate Open) MCR225–8FP MCR225–10FP	V <sub>DRM</sub> , VRRM	600 800	Volts
On-State RMS Current (T <sub>C</sub> = +70°C) (180° Conduction Angles)	IT(RMS)	25	Amps
Peak Non–repetitive Surge Current (1/2 Cycle, Sine Wave 60 Hz, T <sub>C</sub> = +70°C)	ITSM	300	Amps
Circuit Fusing (t = 8.3 ms)	I <sup>2</sup> t	375	A <sup>2</sup> s
Forward Peak Gate Power $(T_C = +70^{\circ}C, \text{ Pulse Width } \leq 1.0 \mu\text{s})$	Рдм	20	Watts
Forward Average Gate Power (T <sub>C</sub> = +70°C, t = 8.3 ms)	PG(AV)	0.5	Watt
Forward Peak Gate Current $(T_C = +70^{\circ}C, \text{ Pulse Width } \leq 1.0 \mu\text{s})$	I <sub>GM</sub>	2.0	Amps
RMS Isolation Voltage ( $T_A = 25^{\circ}C$ , Relative Humidity $\leq 20\%$ ) (%)	V <sub>(ISO)</sub>	1500	Volts
Operating Junction Temperature Range	TJ	-40 to +125	°C
Storage Temperature Range	T <sub>stg</sub>	-40 to +150	°C

<sup>(1)</sup> VDRM and VRRM for all types can be applied on a continuous basis. Ratings apply for zero or negative gate voltage; however, positive gate voltage shall not be applied concurrent with negative potential on the anode. Blocking voltages shall not be tested with a constant current source such that the voltage ratings of the devices are exceeded.

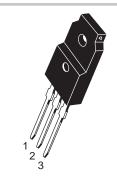


### **ON Semiconductor**

http://onsemi.com

## ISOLATED SCRs (%) 25 AMPERES RMS 600 thru 800 VOLTS





ISOLATED TO-220 Full Pack CASE 221C STYLE 2

PIN ASSIGNMENT			
1	Cathode		
2	Anode		
3	Gate		

#### ORDERING INFORMATION

Device	Device Package	
MCR225-8FP	ISOLATED TO220FP	500/Box
MCR225-10FP	ISOLATED TO220FP	500/Box

**Preferred** devices are recommended choices for future use and best overall value.

#### THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction to Case	$R_{\theta JC}$	1.5	°C/W
Thermal Resistance, Case to Sink	$R_{\theta}CS$	2.2 (typ)	°C/W
Thermal Resistance, Junction to Ambient	$R_{\theta JA}$	60	°C/W
Maximum Lead Temperature for Soldering Purposes 1/8" from Case for 10 Seconds	TL	260	°C

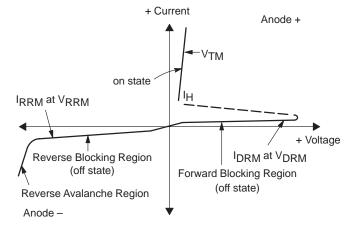
## **ELECTRICAL CHARACTERISTICS** (T<sub>C</sub> = 25°C unless otherwise noted.)

Characteristic	Symbol	Min	Тур	Max	Unit
OFF CHARACTERISTICS	•		•		•
Peak Repetitive Forward or Reverse Blocking Current $(V_D = Rated \ V_{DRM}, \ V_{RRM}; \ Gate \ Open)$ $T_J = 25^{\circ}C$ $T_J = 125^{\circ}C$	IDRM, IRRM	_	_	10 2	μA mA
ON CHARACTERISTICS	•				•
Peak Forward On–State Voltage <sup>(1)</sup> (I <sub>TM</sub> = 50 A)	Vтм		_	1.8	Volts
Gate Trigger Current (Continuous dc) (V <sub>AK</sub> = 12 Vdc, R <sub>L</sub> = 100 Ohms)	lGT		_	40	mA
Gate Trigger Voltage (Continuous dc) (V <sub>AK</sub> = 12 Vdc, R <sub>L</sub> = 100 Ohms)	V <sub>GT</sub>		0.8	1.5	Volts
Gate Non-Trigger Voltage (V <sub>AK</sub> = 12 Vdc, R <sub>L</sub> = 100 Ohms, T <sub>J</sub> = 125°C)	V <sub>GD</sub>	0.2	_	_	Volts
Holding Current (VAK = 12 Vdc, Initiating Current = 200 mA, Gate Open)	lн	_	20	40	mA
Turn-On Time (I <sub>TM</sub> = 25 A, I <sub>GT</sub> = 40 mAdc)	<sup>t</sup> gt	_	1.5	_	μs
Turn-Off Time (V <sub>DRM</sub> = Rated Voltage) (I <sub>TM</sub> = 25 A, I <sub>R</sub> = 25 A) (I <sub>TM</sub> = 25 A, I <sub>R</sub> = 25 A, T <sub>J</sub> = 125°C)	<sup>t</sup> q		15 35		μѕ
DYNAMIC CHARACTERISTICS	-				
Critical Rate-of-Rise of Off-State Voltage (Gate Open, V <sub>D</sub> = Rated V <sub>DRM</sub> , Exponential Waveform)	dv/dt	_	100	_	V/µs

<sup>(1)</sup> Pulse Test: Pulse Width = 1.0 ms, Duty Cycle ≤ 2%.

### **Voltage Current Characteristic of SCR**

Symbol	Parameter
V <sub>DRM</sub>	Peak Repetitive Off State Forward Voltage
IDRM	Peak Forward Blocking Current
VRRM	Peak Repetitive Off State Reverse Voltage
IRRM	Peak Reverse Blocking Current
VTM	Peak on State Voltage
lн	Holding Current



#### **TYPICAL CHARACTERISTICS**

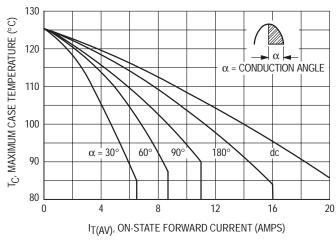


Figure 1. Average Current Derating

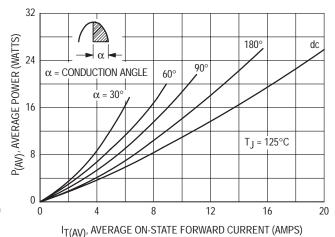
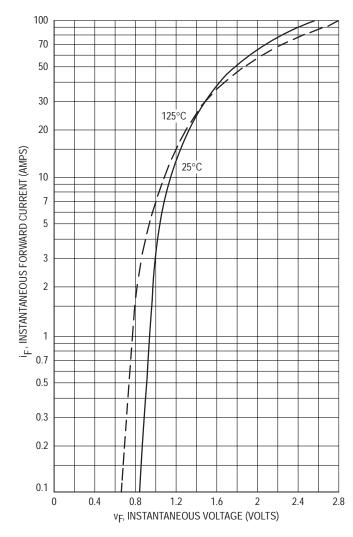


Figure 2. Maximum On-State Power Dissipation



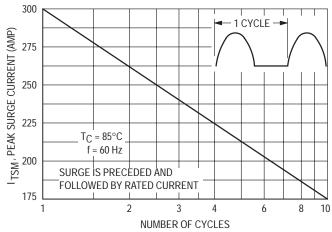


Figure 3. Maximum Forward Voltage

Figure 4. Maximum Non-Repetitive Surge Current

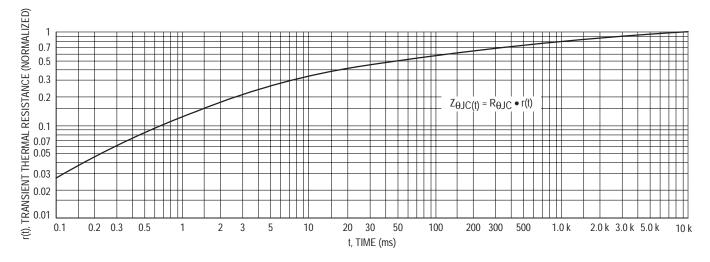


Figure 5. Thermal Response

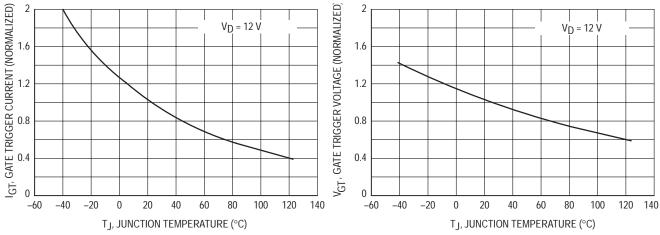


Figure 6. Typical Gate Trigger Current versus Temperature

Figure 7. Typical Gate Trigger Voltage versus Temperature

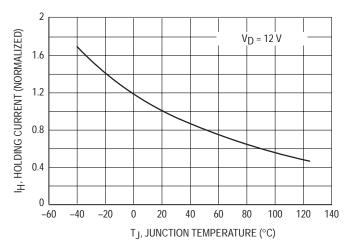
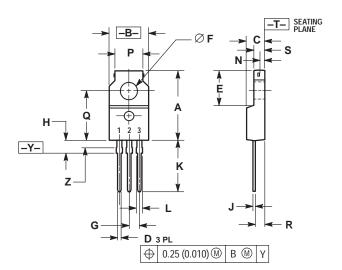


Figure 8. Typical Holding Current versus Temperature

### **PACKAGE DIMENSIONS**

### ISOLATED TO-220 Full Pack

CASE 221C-02 ISSUE C



- NOTES:

  1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.

  2. CONTROLLING DIMENSION: INCH.

  3. LEAD DIMENSIONS UNCONTROLLED WITHIN DIMENSION Z.

	INCHES		MILLIMETERS	
DIM	MIN	MAX	MIN	MAX
Α	0.680	0.700	17.28	17.78
В	0.388	0.408	9.86	10.36
С	0.175	0.195	4.45	4.95
D	0.025	0.040	0.64	1.01
Ε	0.340	0.355	8.64	9.01
F	0.140	0.150	3.56	3.81
G	0.100 BSC		2.54	BSC
Н	0.110	0.155	2.80	3.93
J	0.018	0.028	0.46	0.71
K	0.500	0.550	12.70	13.97
L	0.045	0.070	1.15	1.77
N	0.049		1.25	
Р	0.270	0.290	6.86	7.36
Q	0.480	0.500	12.20	12.70
R	0.090	0.120	2.29	3.04
S	0.105	0.115	2.67	2.92
Z	0.070	0.090	1.78	2.28

PIN 1. CATHODE 2. ANODE 3. GATE

# **Notes**

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